Electronic Supplementary Information (ESI)

Impact of Band-gap Graded Structures Artificially Implemented in Mg-ZnO Epitaxial Films on Photoelectrochemical Properties

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	Sample Mg-0	Sample Mg-3	Sample Mg-5	Sample Mg-8	Sample Mg-10
Mg by WDS	0	-	10.5	15.3	18.0

Fable S1	Mg com	position	estimated	by	WDS
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Figure S1 XRD patterns of Mg-doped ZnO films with different nominal Mg compositions of 0 to 10 at%.



Figure S2 Tauc plots from the optical absorption spectra of Mg-doped ZnO films with different nominal Mg compositions of 0 to10 at%. The arrows indicate the peak positions assigned to an excitonic absorption.



Figure S3 Linear relationships of the band gap, the *c*-axis length and the Urbach energy to the Mg composition. Here, it should be noted that the data points for Sample Mg-3 were missing in the plots due to no WDS data of its Mg composition as listed in Table S1.



Figure S4 For ZnO, Mg:ZnO, up-grade and down-grade Mg-ZnO films, (a) XRD patterns in linear scale intensity, (b) Plots of the *a*- and *c*-axis parameters, the FWHM values of the 0002 peak in the θ -2 θ scan, and the Urbach energy values.